

60V, 3 A NPN high power bipolar transistor 10 January 2014

Product data sheet

1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT60603PY

2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AECQ-101 qualified.

3. Applications

- Power management
- Load switch

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- Linear mode voltage regulator
- Backlighting apllications

4. Quick reference data

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Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	60	V
I _C	collector current		-	-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	8	А
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 3 A; I_{B} = 300 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	60	90	mΩ



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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	mb	С
2	E	emitter		в
3	E emitter	q	- h a	
4	В	base	មុច្ចុថ្	E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	Syn1125

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PHPT60603NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT60603NY	0603NAB

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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

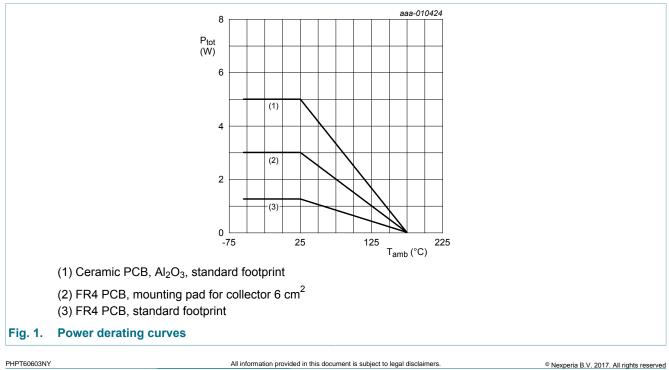
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	А
I _B	base current			-	0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².

[3] Device mounted on an ceramic PCB; AI_2O_3 , standard footprint.

[4] Power dissipation from junction to mounting base.



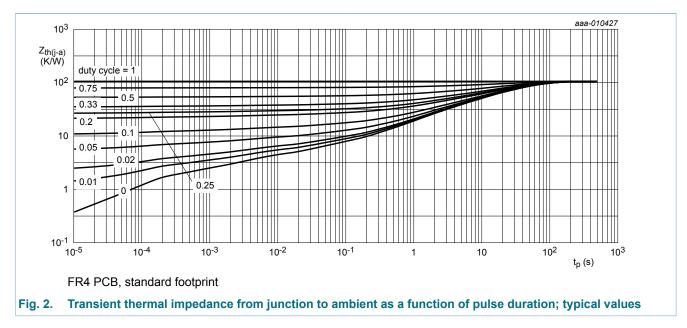
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9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[<u>2]</u>	-	-	50	K/W
			[3]	-	-	30	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

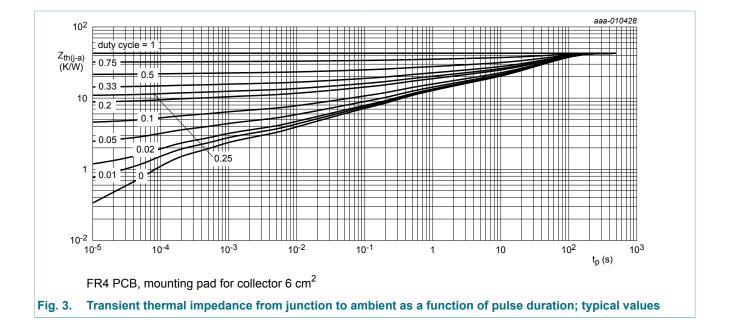
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



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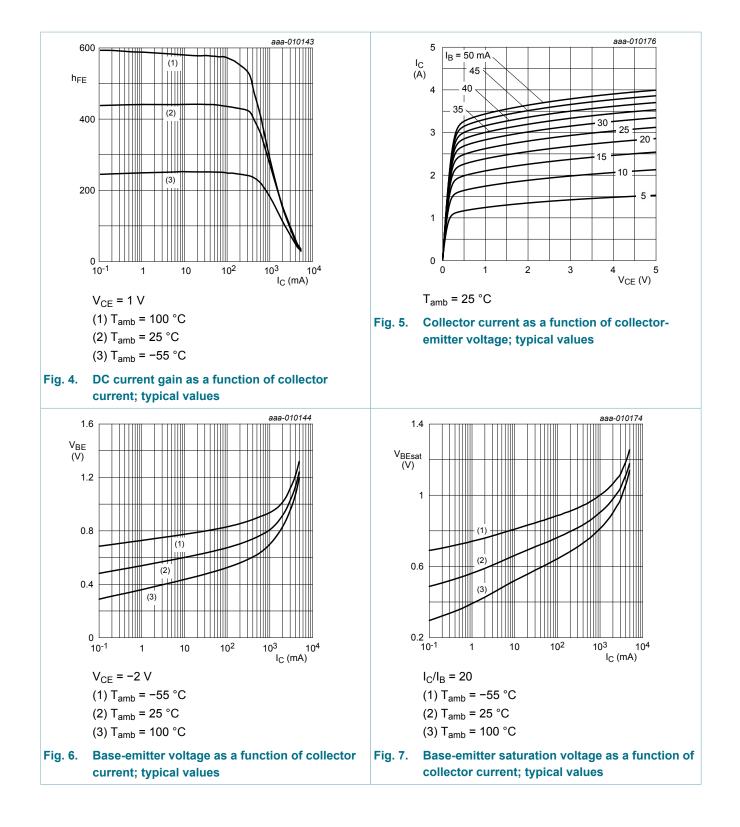


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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 48 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = 48 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I _C = 500 mA; T _{amb} = 25 °C	200	400	-	
		$V_{CE} = 2 \text{ V; } I_C = 1 \text{ A; } t_p \le 300 \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	200	330	-	
		$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 2 \text{ A}; \text{t}_{p} \le 300 \mu\text{s};$ $\delta \le 0.02 ; \text{T}_{amb} = 25 ^{\circ}\text{C}$	100	180	-	
		$V_{CE} = 2 \text{ V; } I_C = 3 \text{ A; } t_p \le 300 \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C; pulsed}$	50	100	-	
OLUUI	collector-emitter saturation voltage	$\begin{split} I_C = 1 \text{ A}; \ I_B = 50 \text{ mA}; \ t_p \leq 300 \mu\text{s}; \\ \delta \leq 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}\text{; } \text{pulsed} \end{split}$	-	70	120	mV
		I_{C} = 3 A; I_{B} = 300 mA; pulsed;	-	180	270	mV
R _{CEsat}	collector-emitter saturation resistance	$t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^\circ C$	-	60	90	mΩ
V _{BEsat}	base-emitter saturation voltage	$\begin{split} I_{C} &= 1 \text{ A}; \ I_{B} = 100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \ \delta &\leq 0.02 \text{ ; } T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	0.86	1	V
		$\begin{split} I_{C} &= 2 \text{ A}; I_{B} = 200 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta &\leq 0.02 \text{ ; } T_{\text{amb}} = 25 ^{\circ}\text{C} \end{split}$	-	1	1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.1 A; T_{amb} = 25 °C	-	0.65	0.85	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A;	-	15	-	ns
tr	rise time	I _{Boff} = -0.05 A; T _{amb} = 25 °C	-	120	-	ns
t _{on}	turn-on time		-	135	-	ns
t _s	storage time		-	800	-	ns
t _f	fall time		-	300	-	ns
t _{off}	turn-off time		-	1100	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	17	-	pF

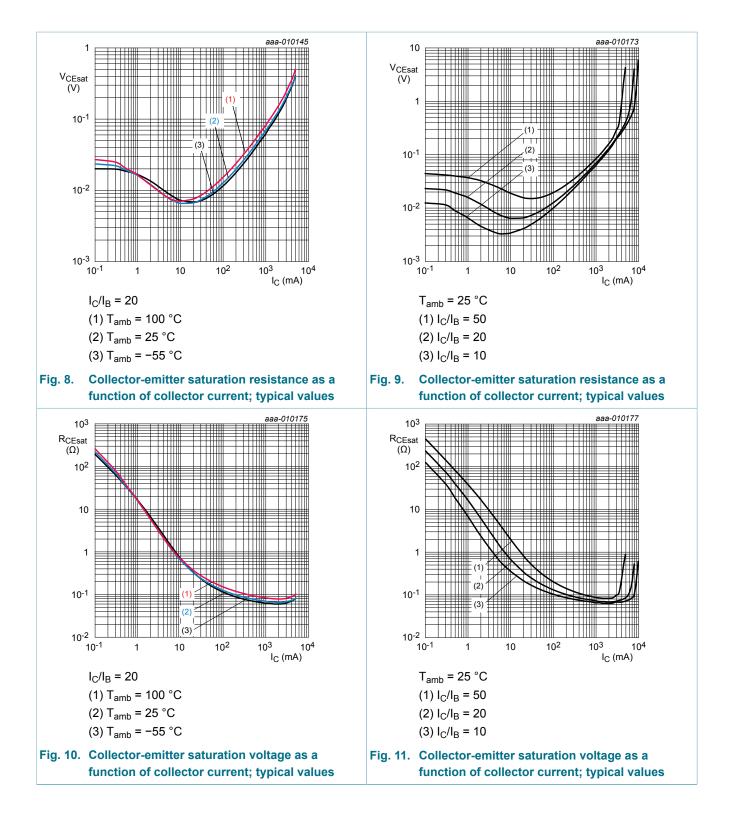
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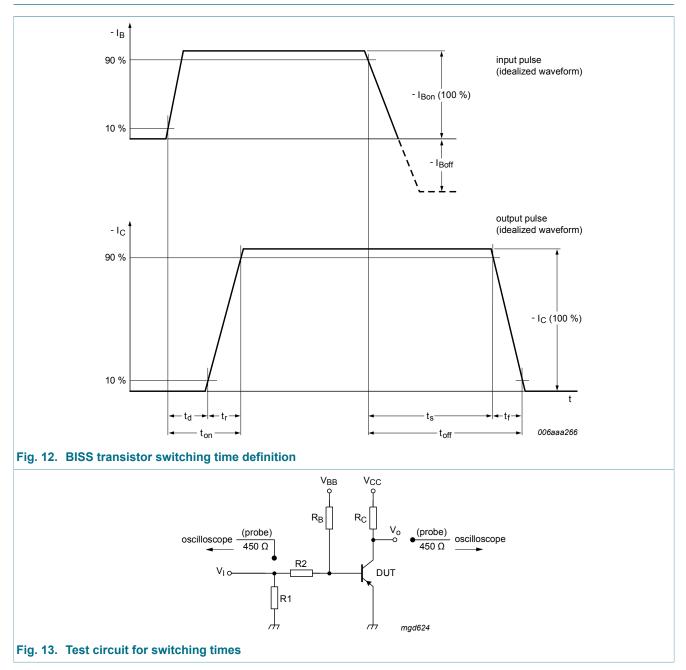
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11. Test information

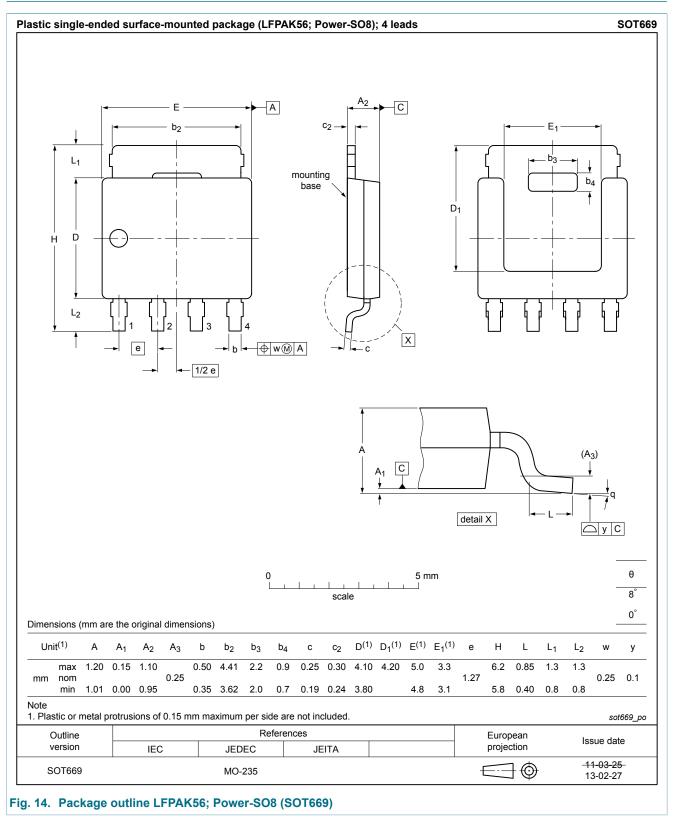


This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



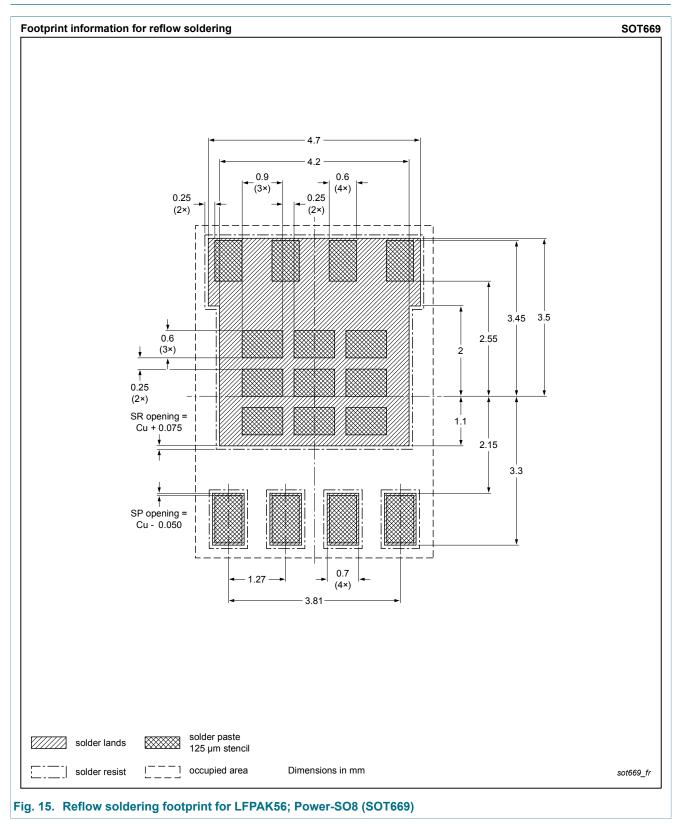
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13. Soldering



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14. Revision history

Table 8. Revision hi	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60603NY v.1	20131213	Product data sheet	-	-
Modifications:	editorial update			
PHPT60603NY v.2	20140110	Product data sheet	-	PHPT60603NY v.1

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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